



2DB1184Q

#### **50V PNP MEDIUM POWER TRANSISTOR IN TO252**

#### **Features**

- BV<sub>CEO</sub> > -50V
- I<sub>C</sub> = -3A High Continuous Collector Current
- I<sub>CM</sub> = -4.5A Peak Pulse Current
- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Voltage
- Ideal for Medium Power Switching or Amplification Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

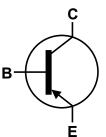
#### **Mechanical Data**

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.34 grams (approximate)

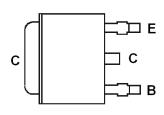








**Device Schematic** 



Pin Out Configuration Top view

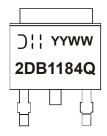
### Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
2DB1184Q-13	AEC-Q101	2DB1184Q	13	16	2,500

Notes

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



2DB1184Q = Product Type Marking Code

Old = Manufacturers' code marking

YYWW = Date Code Marking

YY = Last Digit of Year, (ex: 14 = 2014)

WW = Week Code 01-52



### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-50	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Continuous Collector Current	Ic	-3	A
Peak Pulse Collector Current	I <sub>CM</sub>	-4.5	Α

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	$P_D$	1.2	W
Power Dissipation @T <sub>L</sub> = +25°C (Note 6)		P <sub>D</sub>	15	W
Thermal Resistance, Junction to Lead (Note 5)		$R_{ heta JA}$	104	°C/W
Thermal Resistance, Junction to Ambient (Note 6)		R <sub>0JL</sub>	8.3	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

## ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

- 5. For a device mounted with the exposed collector pad on minimum recommended pad (MRP) layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Thermal resistance from junction to solder-point (on the exposed collector pad).
  7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

### Thermal Characteristics

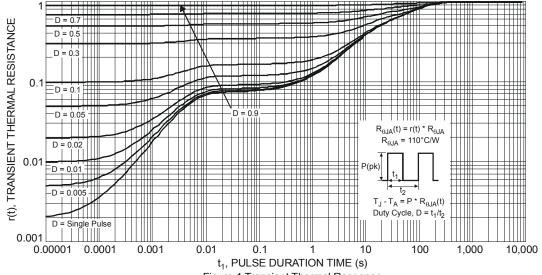


Figure 1 Transient Thermal Response



## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-60	-	_	V	$I_C = -50\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-50	-	_	V	$I_{C} = -1 \text{mA}, I_{B} = 0$	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5	-	_	V	$I_E = -50\mu A, I_C = 0$	
Collector Cutoff Current	I <sub>CBO</sub>	_	_	-1	μΑ	V <sub>CB</sub> = -40V, I <sub>E</sub> = 0	
Emitter Cutoff Current	I <sub>EBO</sub>	-	-	-1	μΑ	$V_{EB} = -4V, I_{C} = 0$	
ON CHARACTERISTICS (Note 8)	ON CHARACTERISTICS (Note 8)						
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_		-1	V	$I_C = -2A$ , $I_B = -0.2A$	
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>		1	-1.2	V	$I_C = -1.5A$ , $I_B = -0.15A$	
DC Current Gain	h <sub>FE</sub>	120		270	_	$V_{CE} = -3V, I_{C} = -0.5A$	
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product	f⊤	_	110	_	MHz	$V_{CE} = -5V$ , $I_{C} = -0.1A$ , $f = 30MHz$	
Output Capacitance	C <sub>obo</sub>	-	26	_	pF	V <sub>CB</sub> = -10V, f = 1MHz	
Turn-On Time	t <sub>on</sub>	-	109	_	ns		
Delay Time	t <sub>d</sub>	_	60	_	ns	V <sub>CC</sub> = 30V I <sub>CC</sub> = 150mA I <sub>B1</sub> = - I <sub>B2</sub> = 15mA	
Rise Time	t <sub>r</sub>	_	49	_	ns		
Turn-Off Time	t <sub>off</sub>	_	280	_	ns		
Storage Time	ts	_	246		ns		
Fall Time	t <sub>f</sub>	_	34	_	ns		

Note: 8. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s$ . Duty cycle  $\leq 2\%$ .

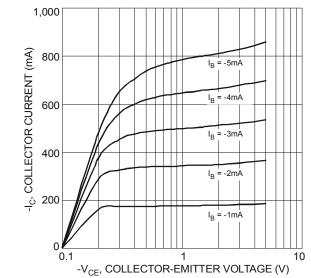


Figure 2 Typical Collector Current vs. Collector-Emitter Voltage

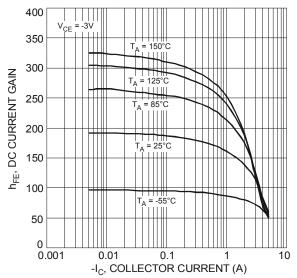


Figure 3 Typical DC Current Gain vs. Collector Current



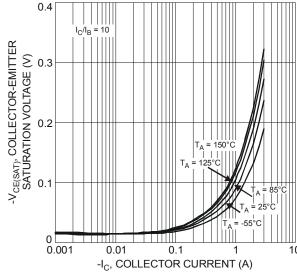


Figure 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

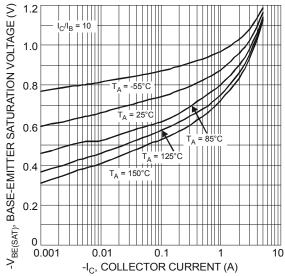


Figure 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

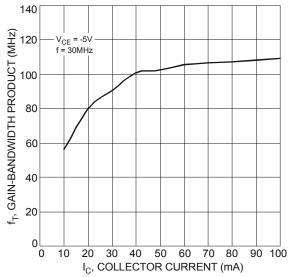


Figure 8 Typical Gain-Bandwidth Product vs. Collector Current

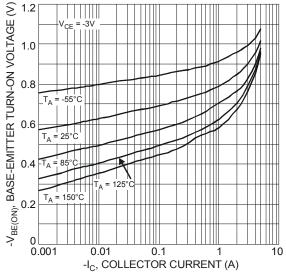


Figure 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

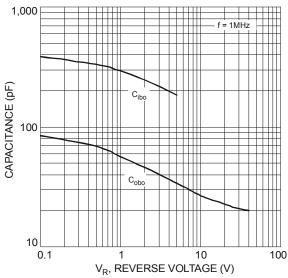
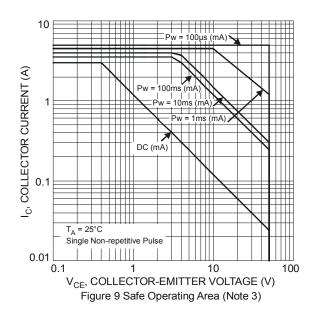


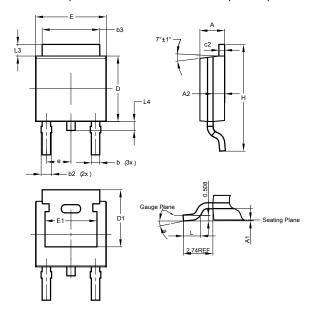
Figure 7 Typical Capacitance Characteristics





## **Package Outline Dimensions**

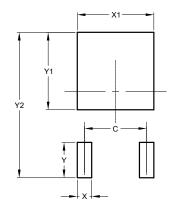
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
c2	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	4.572		
X	1.060		
X1	5.632		
Υ	2.600		
Y1	5.700		
Y2	10.700		



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